

Jochen Bruckbauer

List of Publications by Year in descending order

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36
papers

568
citations

758635

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642321

23
g-index

37
all docs

37
docs citations

37
times ranked

785
citing authors

#	ARTICLE	IF	CITATIONS
1	An Organic Down-Converting Material for White Light Emission from Hybrid LEDs. <i>Advanced Materials</i> , 2014, 26, 7290-7294.	11.1	111
2	High resolution cathodoluminescence hyperspectral imaging of surface features in InGaN/GaN multiple quantum well structures. <i>Applied Physics Letters</i> , 2011, 98, .	1.5	75
3	High-Resolution Cathodoluminescence Hyperspectral Imaging of Nitride Nanostructures. <i>Microscopy and Microanalysis</i> , 2012, 18, 1212-1219.	0.2	51
4	Cool to warm white light emission from hybrid inorganic/organic light-emitting diodes. <i>Journal of Materials Chemistry C</i> , 2016, 4, 11499-11507.	2.7	28
5	Coincident Electron Channeling and Cathodoluminescence Studies of Threading Dislocations in GaN. <i>Microscopy and Microanalysis</i> , 2014, 20, 55-60.	0.2	27
6	Influence of substrate miscut angle on surface morphology and luminescence properties of AlGaIn. <i>Applied Physics Letters</i> , 2014, 104, 092114.	1.5	24
7	Implementing fluorescent MOFs as down-converting layers in hybrid light-emitting diodes. <i>Journal of Materials Chemistry C</i> , 2019, 7, 2394-2400.	2.7	23
8	Electron channelling contrast imaging for III-nitride thin film structures. <i>Materials Science in Semiconductor Processing</i> , 2016, 47, 44-50.	1.9	21
9	Linear oligofluorene-BODIPY structures for fluorescence applications. <i>Journal of Materials Chemistry C</i> , 2013, 1, 2249.	2.7	20
10	Influence of stress on optical transitions in GaN nanorods containing a single InGaIn/GaN quantum disk. <i>Journal of Applied Physics</i> , 2014, 116, .	1.1	18
11	Electron channeling contrast imaging studies of nonpolar nitrides using a scanning electron microscope. <i>Applied Physics Letters</i> , 2013, 102, .	1.5	16
12	Colour tuning in white hybrid inorganic/organic light-emitting diodes. <i>Journal Physics D: Applied Physics</i> , 2016, 49, 405103.	1.3	15
13	Determining GaN Nanowire Polarity and its Influence on Light Emission in the Scanning Electron Microscope. <i>Nano Letters</i> , 2019, 19, 3863-3870.	4.5	14
14	Cathodoluminescence hyperspectral imaging of trench-like defects in InGaIn/GaN quantum well structures. <i>Journal Physics D: Applied Physics</i> , 2014, 47, 135107.	1.3	13
15	Cathodoluminescence studies of chevron features in semi-polar (112̂2) InGaIn/GaN multiple quantum well structures. <i>Journal of Applied Physics</i> , 2018, 123, .	1.1	12
16	Spatially-resolved optical and structural properties of semi-polar $\text{Al}_x\text{Ga}_{1-x}\text{N}$ with x up to 0.56. <i>Scientific Reports</i> , 2017, 7, 10804.	1.6	11
17	Probing light emission from quantum wells within a single nanorod. <i>Nanotechnology</i> , 2013, 24, 365704.	1.3	10
18	A systematic comparison of polar and semipolar Si-doped AlGaIn alloys with high AlN content. <i>Journal Physics D: Applied Physics</i> , 2021, 54, 035302.	1.3	9

#	ARTICLE	IF	CITATIONS
19	Scanning electron microscopy as a flexible technique for investigating the properties of UV-emitting nitride semiconductor thin films. <i>Photonics Research</i> , 2019, 7, B73.	3.4	9
20	Crystalline grain engineered CsPbI ₃ Br ₂ films for indoor photovoltaics. <i>Applied Surface Science</i> , 2022, 592, 152865.	3.1	8
21	Optical investigation of semi-polar (11-22) Al _x Ga _{1-x} N with high Al composition. <i>Applied Physics Letters</i> , 2017, 110, .	1.5	7
22	Structural and luminescence imaging and characterisation of semiconductors in the scanning electron microscope. <i>Semiconductor Science and Technology</i> , 2020, 35, 054001.	1.0	7
23	A poly(urethane)-encapsulated benzo[2,3- <i>d</i> :6,7- <i>d'</i>]imidazole organic down-converter for green hybrid LEDs. <i>Materials Chemistry Frontiers</i> , 2020, 4, 1006-1012.	3.2	7
24	Monolithic multiple colour emission from InGa _N grown on patterned non-polar GaN. <i>Scientific Reports</i> , 2019, 9, 986.	1.6	6
25	Optical Properties of GaN Nanorods Containing a Single or Multiple InGa _N Quantum Wells. <i>Japanese Journal of Applied Physics</i> , 2013, 52, 08JE11.	0.8	4
26	Self-assembly of ordered wurtzite/rock salt heterostructures – A new view on phase separation in Mg _x Zn _{1-x} O. <i>Journal of Applied Physics</i> , 2015, 118, .	1.1	4
27	Influence of an InGa _N superlattice pre-layer on the performance of semi-polar (11-22) green LEDs grown on silicon. <i>Scientific Reports</i> , 2020, 10, 12650.	1.6	4
28	Light-Emitting Diodes: An Organic Down-Converting Material for White-Light Emission from Hybrid LEDs (<i>Adv. Mater.</i> 43/2014). <i>Advanced Materials</i> , 2014, 26, 7415-7415.	11.1	3
29	Luminescence behavior of semipolar (10-11) InGa _N /Ga _N bow-tie structures on patterned Si substrates. <i>Journal of Applied Physics</i> , 2020, 127, 035705.	1.1	3
30	Influence of micro-patterning of the growth template on defect reduction and optical properties of non-polar (11-22) Ga _N . <i>Journal Physics D: Applied Physics</i> , 2021, 54, 025107.	1.3	3
31	Applications of electron channeling contrast imaging for characterizing nitride semiconductor thin films. <i>Microscopy and Microanalysis</i> , 2012, 18, 684-685.	0.2	1
32	You Do What in Your Microprobe?! The EPMA as a Multimode Platform for Nitride Semiconductor Characterization. <i>Microscopy and Microanalysis</i> , 2018, 24, 2026-2027.	0.2	1
33	Electron Channeling Contrast Imaging of Defects in III-Nitride Semiconductors. <i>Microscopy and Microanalysis</i> , 2014, 20, 1024-1025.	0.2	0
34	Cathodoluminescence Hyperspectral Imaging of Nitride Semiconductors: Introducing New Variables. <i>Microscopy and Microanalysis</i> , 2014, 20, 906-907.	0.2	0
35	Reprint of: Electron channelling contrast imaging for III-nitride thin film structures. <i>Materials Science in Semiconductor Processing</i> , 2016, 55, 19-25.	1.9	0
36	Advances in electron channelling contrast imaging and electron backscatter diffraction for imaging and analysis of structural defects in the scanning electron microscope. <i>IOP Conference Series: Materials Science and Engineering</i> , 2020, 891, 012023.	0.3	0